MY20N15D

150V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

The MY20N15D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

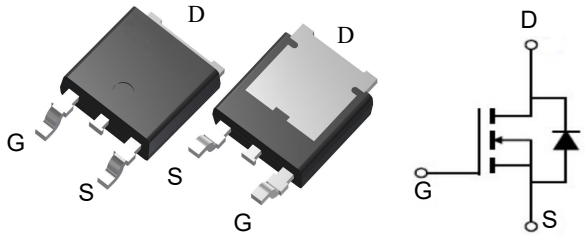
RoHS Compliant

Features

V_{DSS}	150	V
I_D	20	A
$R_{DS(ON)}$(atV_{GS}=10V)	95	mΩ
$R_{DS(ON)}$(atV_{GS}=4.5V)	105	mΩ

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY20N15D	TO-252-2L	MY20N15D	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	20	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	14	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	3	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	2.5	A
I_{DM}	Pulsed Drain Current[2]	40	A
EAS	Single Pulse Avalanche Energy[3]	53	mJ
I_{AS}	Avalanche Current	18	A
P_D@T_C=25℃	Total Power Dissipation[3]	72.6	W
P_D@T_A=25℃	Total Power Dissipation[3]	2.1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	60	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	1.72	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance [2]	V_{GS}=10V , I_D=10A	---	95	105	mΩ
	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=10A	---	105	115	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=120V , V_{GS}=0V , T_J=25 ℃	---	---	1	uA
		V_{DS}=120V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	33	---	S
Q_g	Total Gate Charge	V_{DS}=75V , V_{GS}=4.5V , I_D=10A	---	25.1	---	nC
Q_{gs}	Gate-Source Charge		---	6.8	---	
Q_{gd}	Gate-Drain Charge		---	12.6	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=75V , V_{GS}=10V , R_G=3.3 I_D=10A	---	13	---	ns
T_r	Rise Time		---	8.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	25	---	
T_f	Fall Time		---	11	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	2285	---	pF
C_{oss}	Output Capacitance		---	110	---	
C_{rss}	Reverse Transfer Capacitance		---	83	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	20	A
I_{SM}	Pulsed Source Current[2,5]		---	---	40	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=10A , dI/dt=100A/μs , T_J=25℃	---	37	---	nS
Q_{rr}	Reverse Recovery Charge		---	263	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3 .The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.3mH,I_{AS}=18A

4.The power dissipation is limited by 150℃ junction temperature

5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

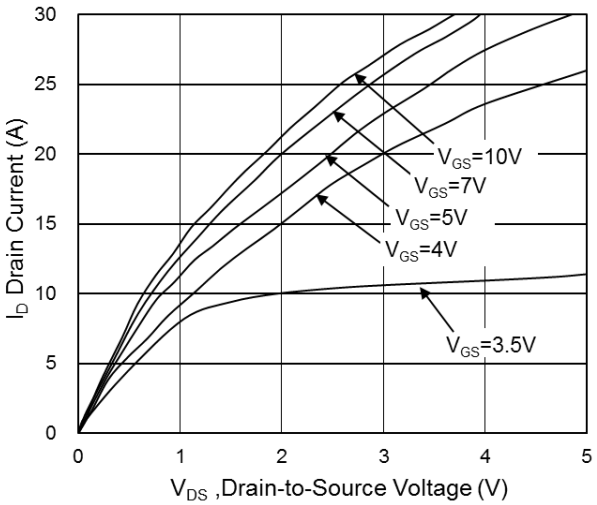


Fig.1 Typical Output Characteristics

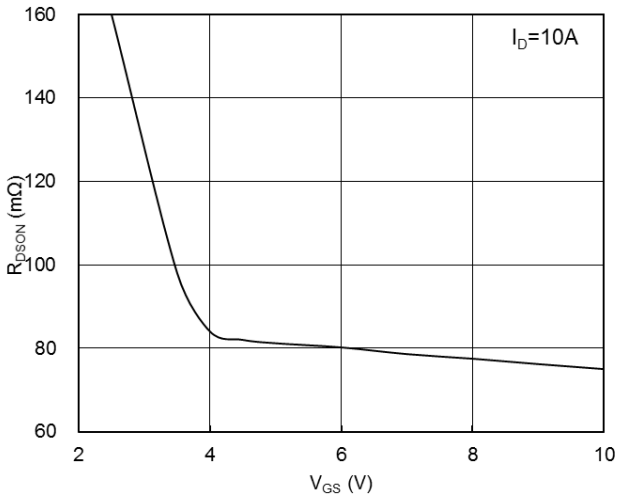


Fig.2 On-Resistance vs. Gate-Source Voltage

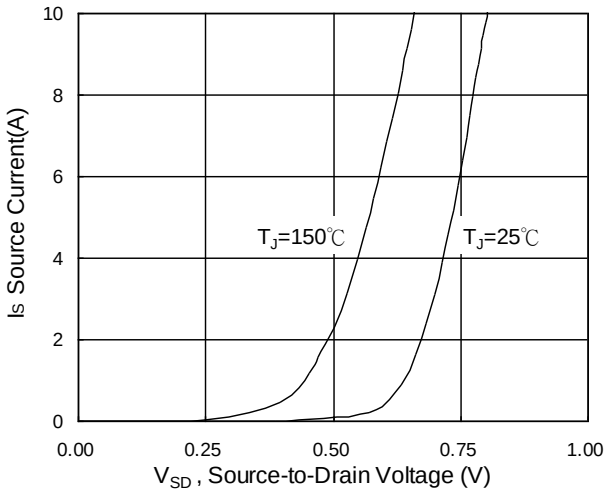


Fig.3 Forward Characteristics of Reverse

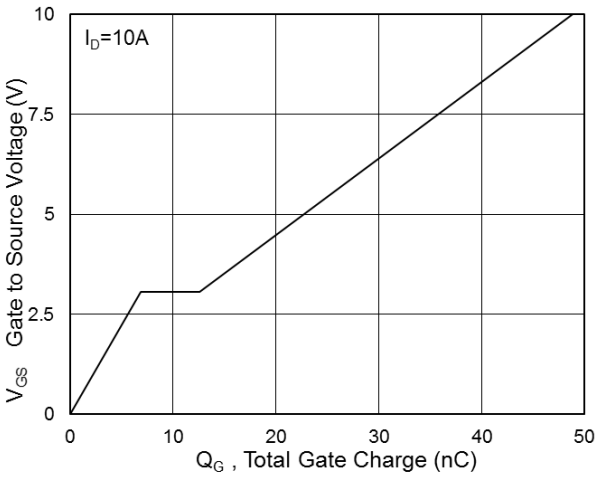


Fig.4 Gate-Charge Characteristics

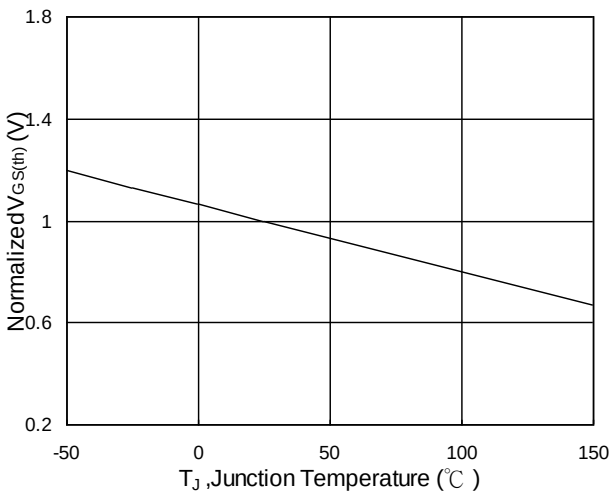


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

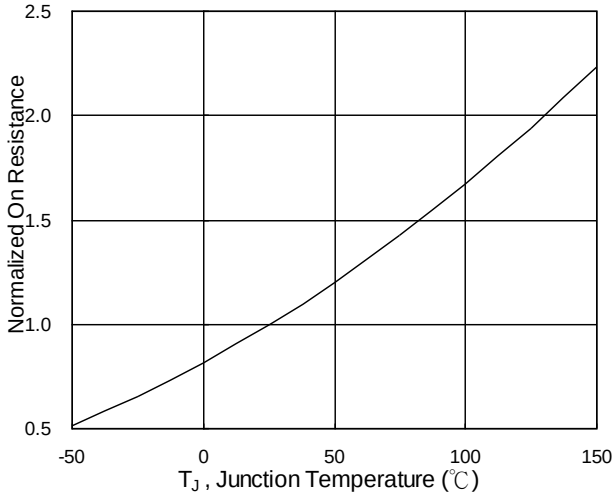


Fig.6 Normalized R_{DSON} vs. T_J

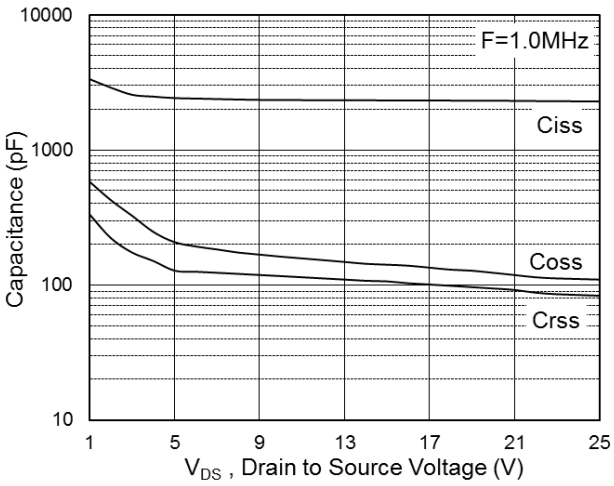


Fig.7 Capacitance

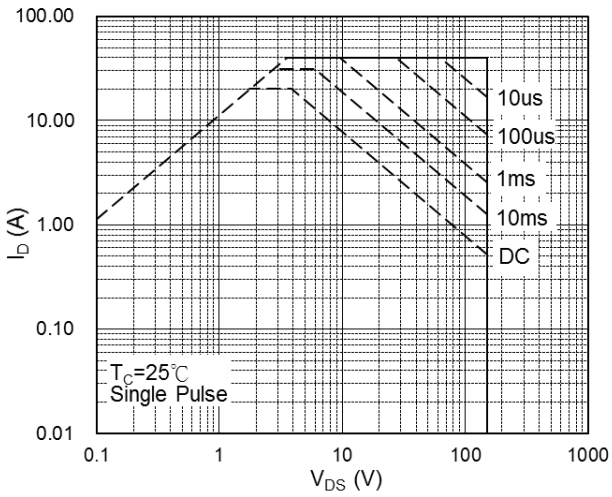


Fig.8 Safe Operating Area

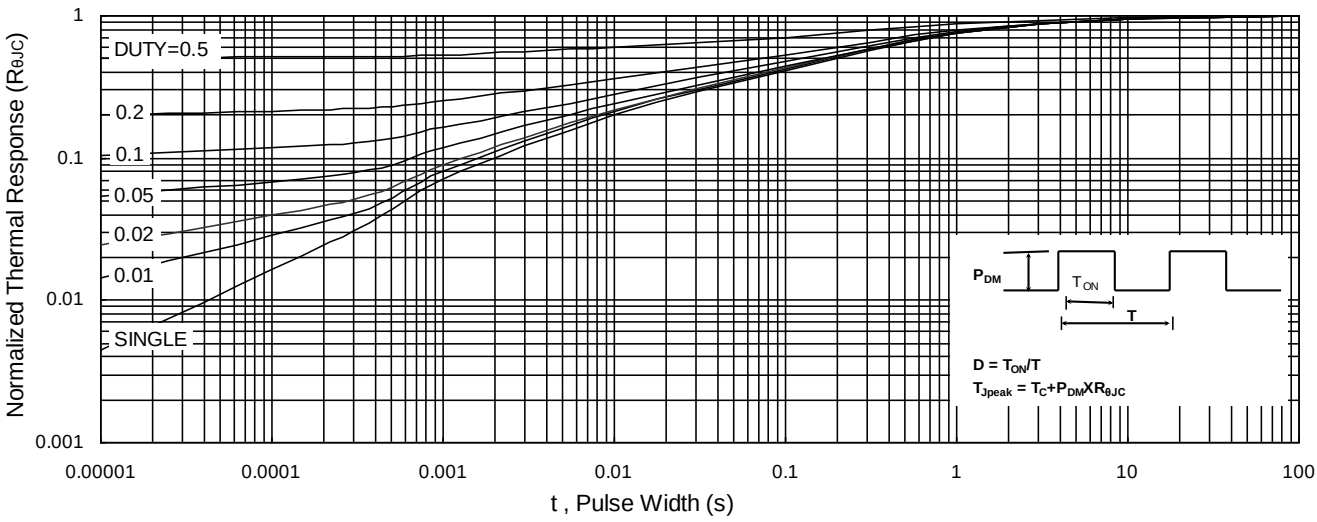


Fig.9 Normalized Maximum Transient Thermal Impedance

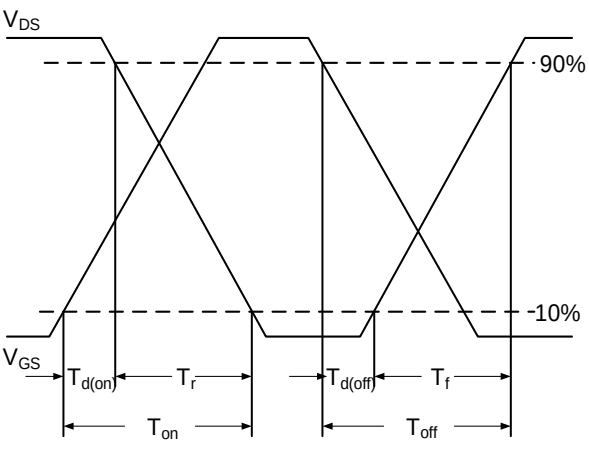


Fig.10 Switching Time Waveform

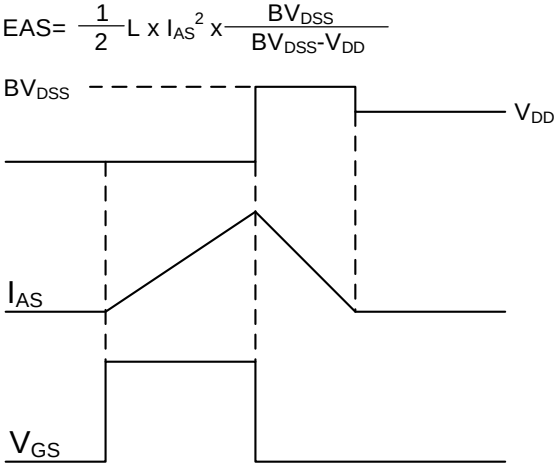
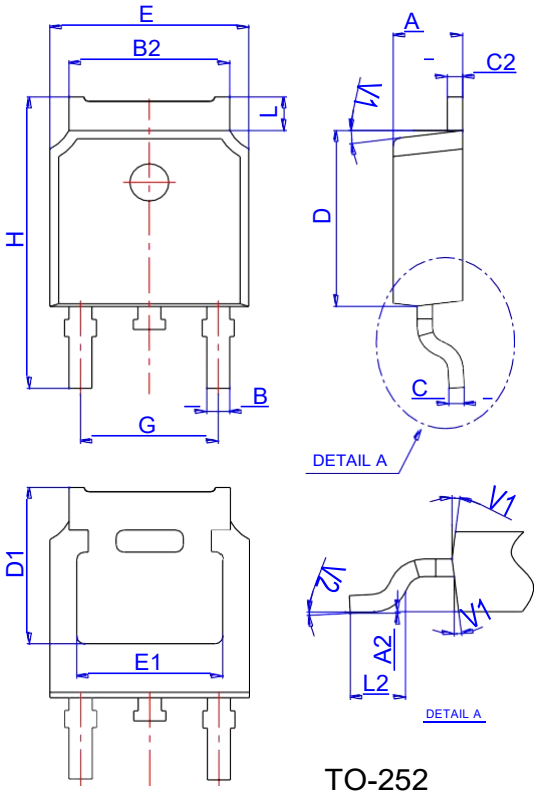


Fig.11 Unclamped Inductive Switching Waveform

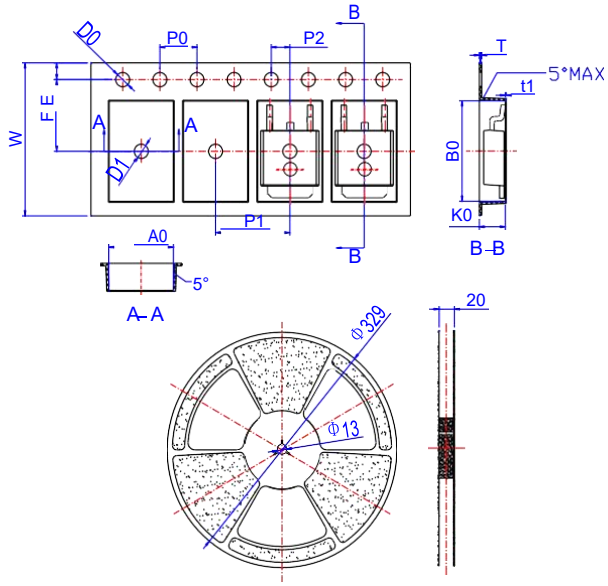
Package Mechanical Data-TO-252-JQ Single



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583